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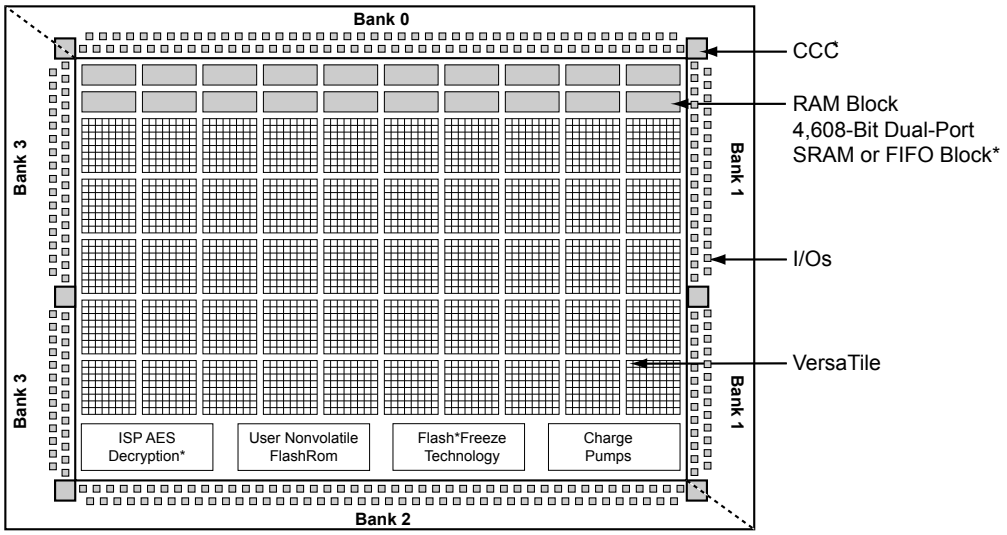
Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1584
Total RAM Bits	18432
Number of I/O	157
Number of Gates	60000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	201-VFBGA, CSBGA
Supplier Device Package	201-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp060v2-csg201



*Note: *Not supported by AGLP030 devices*

Figure 1-1 • **IGLOO PLUS Device Architecture Overview with Four I/O Banks (AGLP030, AGLP060, and AGLP125)**

*Flash*Freeze Technology*

The IGLOO PLUS device has an ultra-low power static mode, called Flash*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash*Freeze technology enables the user to quickly (within 1 µs) enter and exit Flash*Freeze mode by activating the Flash*Freeze pin while all power supplies are kept at their original values. In addition, I/Os and global I/Os can still be driven and can be toggling without impact on power consumption, clocks can still be driven or can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and I/O states. I/Os can be individually configured to either hold their previous state or be tristated during Flash*Freeze mode. Alternatively, they can be set to a certain state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL, and the device consumes as little as 5 µW in this mode.

Flash*Freeze technology allows the user to switch to Active mode on demand, thus simplifying the power management of the device.

The Flash*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. Refer to Figure 1-2 for an illustration of entering/exiting Flash*Freeze mode. It is also possible to use the Flash*Freeze pin as a regular I/O if Flash*Freeze mode usage is not planned.

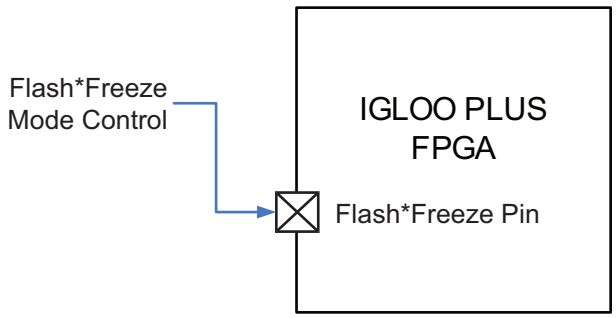


Figure 1-2 • **IGLOO PLUS Flash*Freeze Mode**

SRAM and FIFO

IGLOO PLUS devices (except AGLP030 devices) have embedded SRAM blocks along their north side. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in AGLP030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

IGLOO PLUS devices provide designers with very flexible clock conditioning circuit (CCC) capabilities. Each member of the IGLOO PLUS family contains six CCCs. One CCC (center west side) has a PLL. The AGLP030 device does not have a PLL or CCCs; it contains only inputs to six globals.

The six CCC blocks are located at the four corners and the centers of the east and west sides. One CCC (center west side) has a PLL.

The four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz up to 250 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases (for PLL only) is 40 ps × 250 MHz / f_{OUT_CCC}

Global Clocking

IGLOO PLUS devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

The IGLOO PLUS family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V). IGLOO PLUS FPGAs support many different I/O standards.

The I/Os are organized into four banks. All devices in IGLOO PLUS have four banks. The configuration of these banks determines the I/O standards supported.

Ramping up (V2 devices): 0.65 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.55 V < trip_point_down < 0.95 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V for V5 devices, and 0.75 V ± 0.2 V for V2 devices), the PLL output lock signal goes Low and/or the output clock is lost. Refer to the "Brownout Voltage" section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOO PLUS Device Family User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

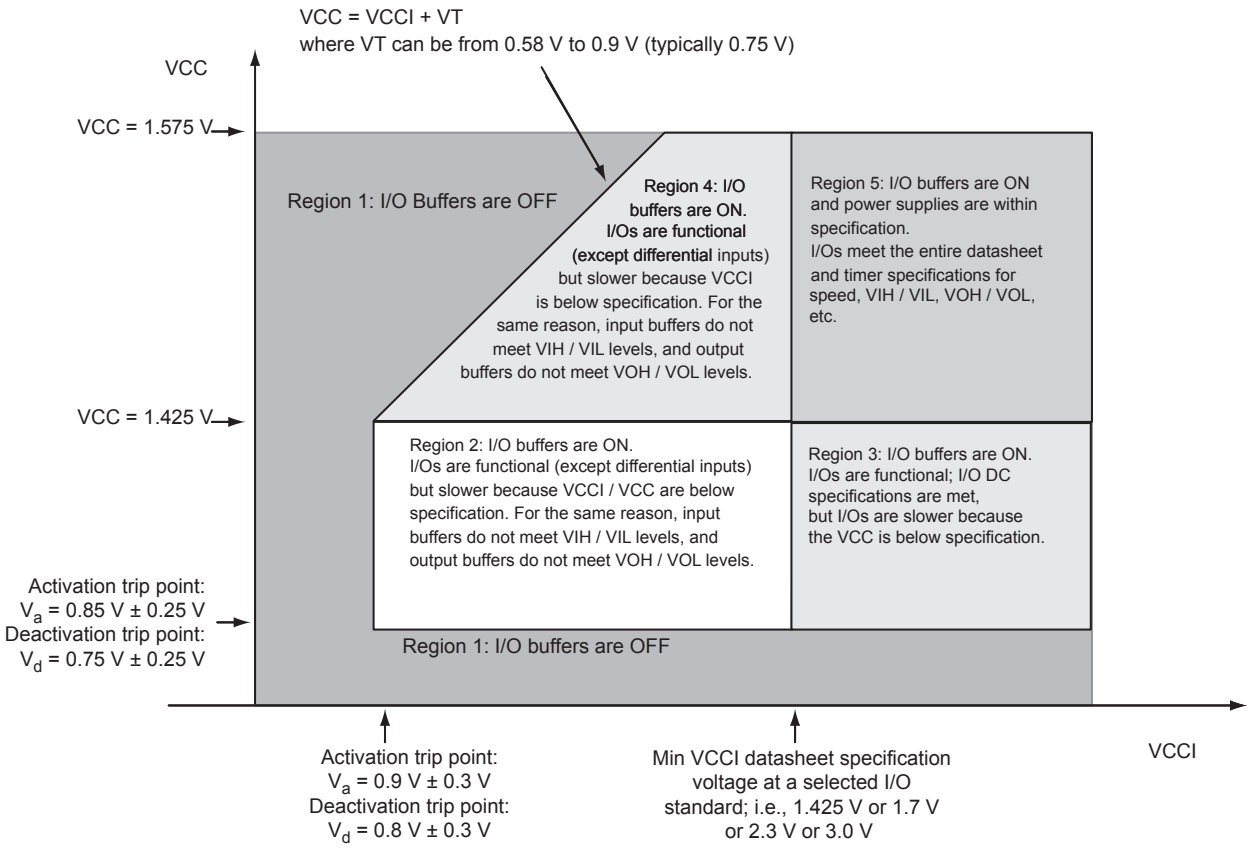


Figure 2-1 • **V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

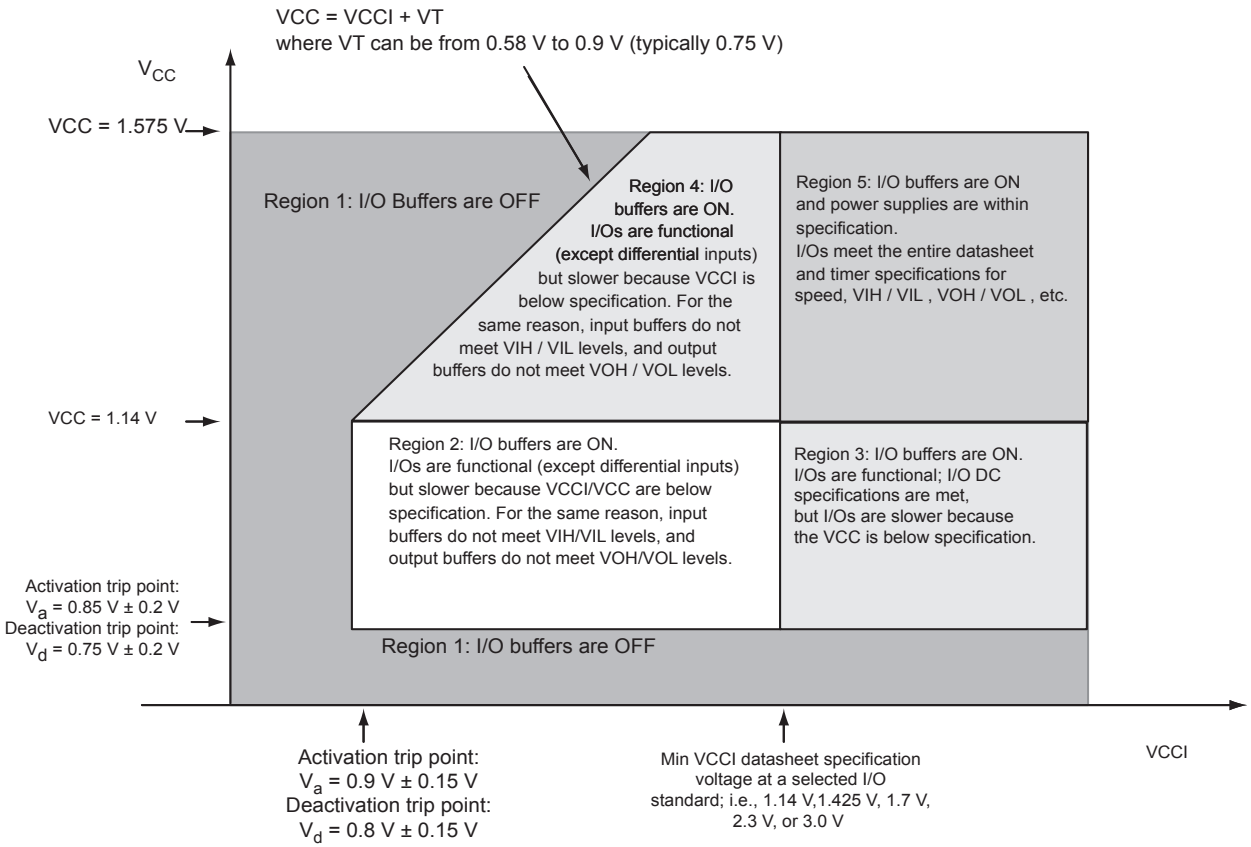


Figure 2-2 • **V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction temperature to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A \qquad \textit{EQ 1}$$

where:

T_A = Ambient temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Figure 2-5.

P = Power dissipation

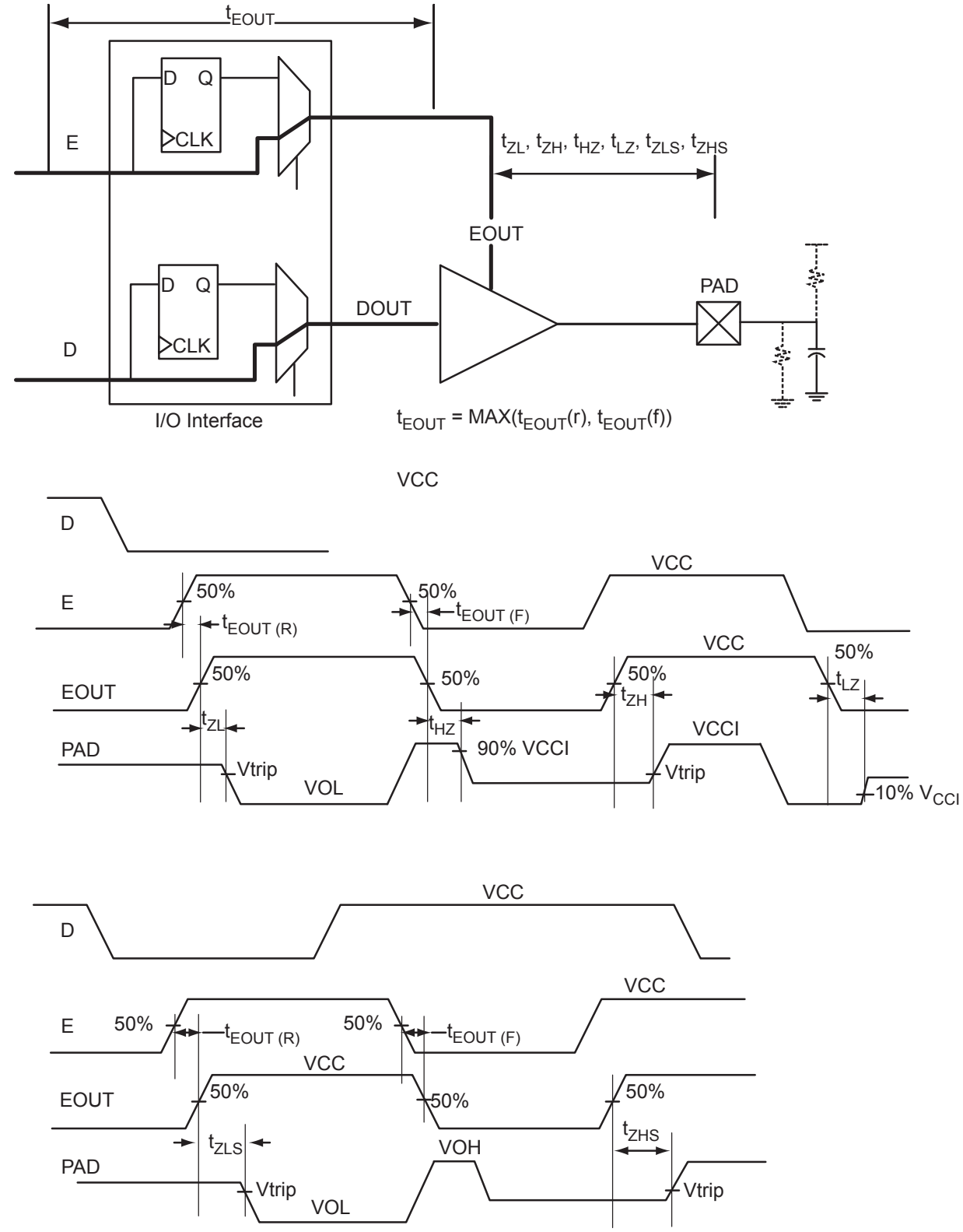


Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (example)**

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-48 • 2.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	4.44	0.18	1.06	1.22	0.66	4.53	4.15	1.80	1.70	ns
6 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
8 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
12 mA	STD	0.97	3.07	0.18	1.06	1.22	0.66	3.14	3.03	2.22	2.48	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-49 • 2.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	2.41	0.18	1.06	1.22	0.66	2.47	2.22	1.79	1.77	ns
6 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
8 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
12 mA	STD	0.97	1.77	0.18	1.06	1.22	0.66	1.81	1.51	2.22	2.56	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-50 • 2.5 LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCC_I = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	5.04	0.19	1.19	1.40	0.67	5.12	4.65	2.22	2.36	ns
6 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
8 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
12 mA	STD	0.98	3.63	0.19	1.19	1.40	0.67	3.69	3.50	2.66	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-51 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	2.96	0.19	1.19	1.40	0.67	3.00	2.67	2.22	2.46	ns
6 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
8 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
12 mA	STD	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

Table 2-64 • Minimum and Maximum DC Input and Output Levels

1.2 V LVCMOS[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

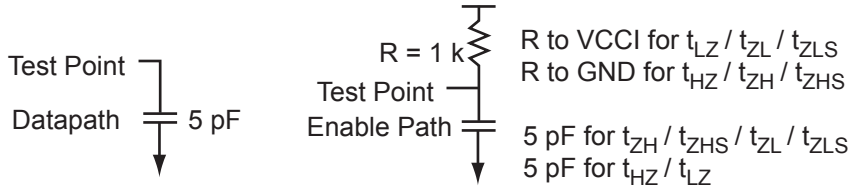


Figure 2-11 • AC Loading

Table 2-65 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.2	0.6	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-66 • 1.2 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	8.27	0.19	1.57	2.34	0.67	7.94	6.77	3.00	3.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-67 • 1.2 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-70 • 1.2 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	STD	0.98	8.27	0.19	1.57	2.34	0.67	7.94	6.77	3.00	3.11	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-71 • 1.2 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	STD	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

***Table 2-73* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-13 on page 2-43 for more information.*

Global Resource Characteristics

AGLP125 Clock Tree Topology

Clock delays are device-specific. Figure 2-21 is an example of a global tree used for clock routing. The global tree presented in Figure 2-21 is driven by a CCC located on the west side of the AGLP125 device. It is used to drive all D-flip-flops in the device.

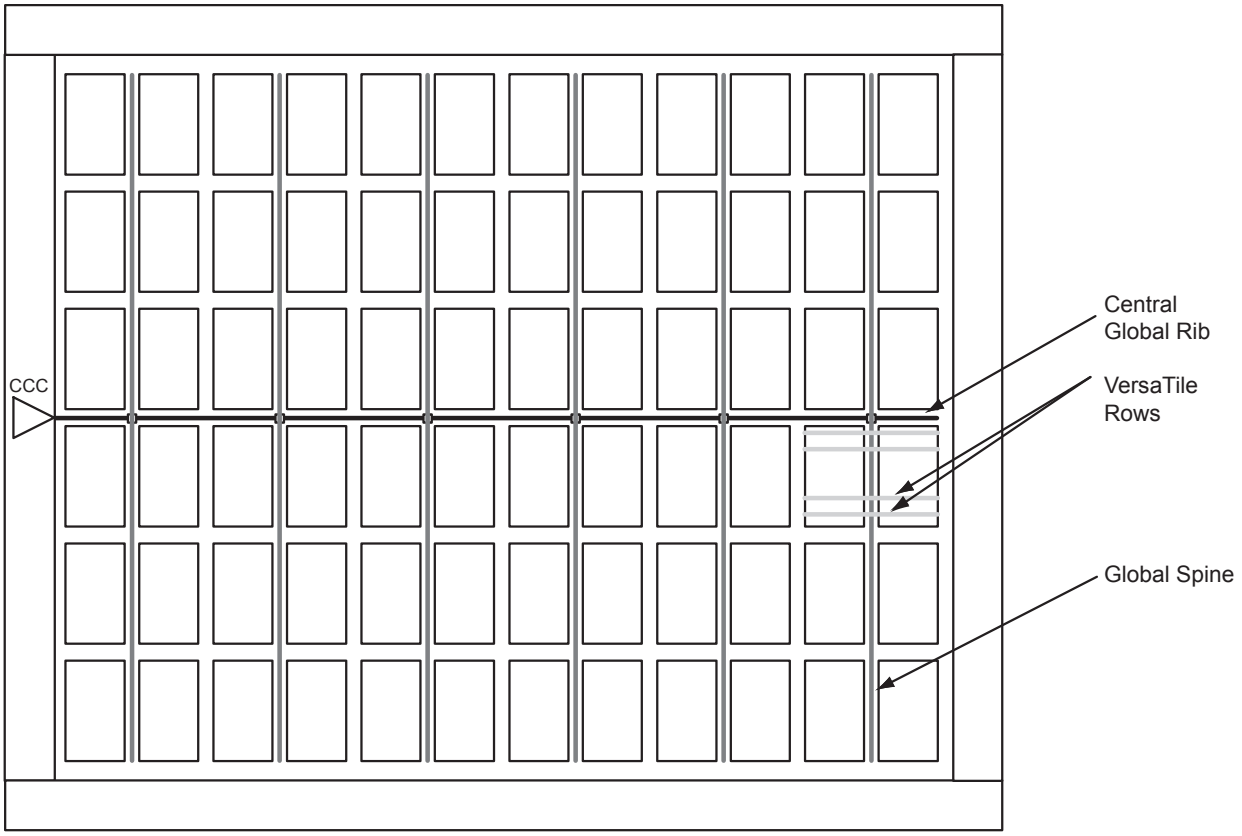


***Figure 2-21* • Example of Global Tree Use in an AGLP125 Device for Clock Routing**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-92 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.68	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{BKS}	BLK setup time	1.37	ns
t_{BKH}	BLK hold time	0.13	ns
t_{DS}	Input data (DIN) setup time	0.59	ns
t_{DH}	Input data (DIN) hold time	0.30	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.94	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.55	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.51	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.29	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.24	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.40	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	1.72	ns
	RESET Low to data out Low on DOUT (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-93 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.61	ns
t_{ENH}	REN, WEN hold time	0.07	ns
t_{DS}	Input data (WD) setup time	0.59	ns
t_{DH}	Input data (WD) hold time	0.30	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	3.51	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.43	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.21	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.25	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	1.72	ns
	RESET Low to data out Low on RD (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.2 V DC Core Voltage

***Table 2-94* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.25	ns
t_{ENH}	REN, WEN hold time	0.25	ns
t_{BKS}	BLK setup time	2.54	ns
t_{BKH}	BLK hold time	0.25	ns
t_{DS}	Input data (DIN) setup time	1.10	ns
t_{DH}	Input data (DIN) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	2.82	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.32	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.21	ns
	RESET Low to data out Low on DOUT (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

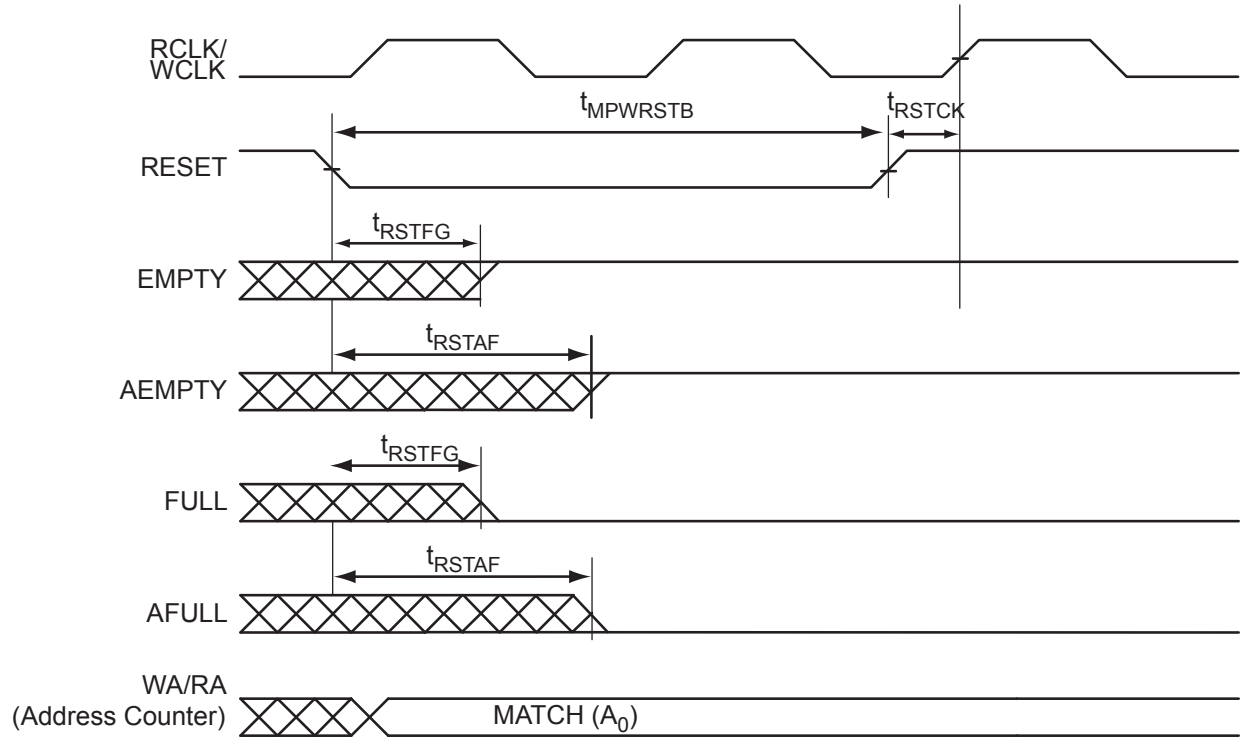


Figure 2-32 • **FIFO Reset**

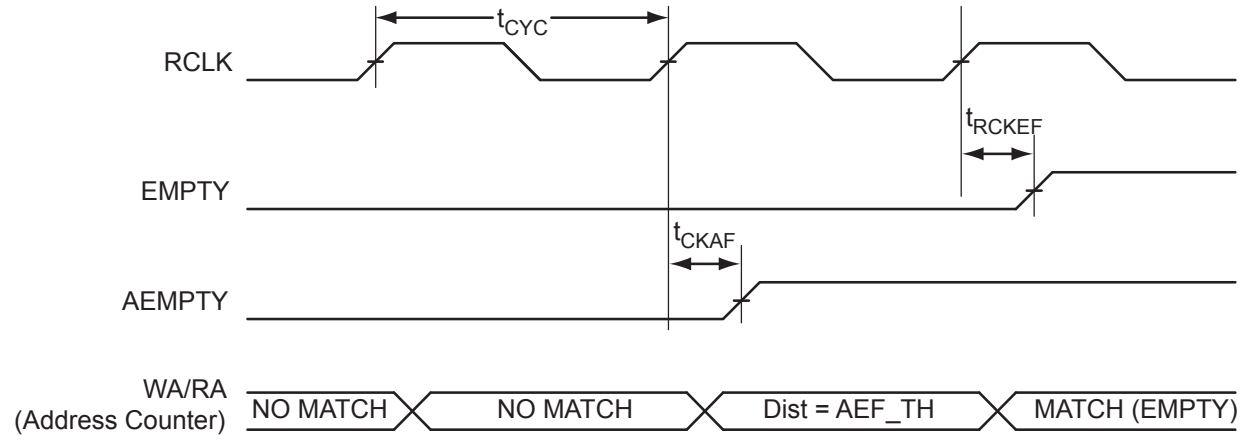


Figure 2-33 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-96 • FIFO

Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.66	ns
t_{ENH}	REN, WEN Hold Time	0.13	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.63	ns
t_{DH}	Input Data (WD) Hold Time	0.20	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.77	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.50	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.94	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.79	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	10.71	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.90	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.68	ns
	RESET Low to Data Out Low on RD (pipelined)	1.68	ns
$t_{REMRSTB}$	RESET Removal	0.51	ns
$t_{RECRSTB}$	RESET Recovery	2.68	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

VQ176	
Pin Number	AGLP060 Function
1	GAA2/IO156RSB3
2	IO155RSB3
3	GAB2/IO154RSB3
4	IO153RSB3
5	GAC2/IO152RSB3
6	GND
7	VCCIB3
8	IO149RSB3
9	IO147RSB3
10	IO145RSB3
11	IO144RSB3
12	IO143RSB3
13	VCC
14	IO141RSB3
15	GFC1/IO140RSB3
16	GFB1/IO138RSB3
17	GFB0/IO137RSB3
18	VCOMPLF
19	GFA1/IO136RSB3
20	VCCPLF
21	GFA0/IO135RSB3
22	GND
23	VCCIB3
24	GFA2/IO134RSB3
25	GFB2/IO133RSB3
26	GFC2/IO132RSB3
27	IO131RSB3
28	IO130RSB3
29	IO129RSB3
30	IO127RSB3
31	IO126RSB3
32	IO125RSB3
33	IO123RSB3
34	IO122RSB3
35	IO121RSB3

VQ176	
Pin Number	AGLP060 Function
36	IO119RSB3
37	GND
38	VCCIB3
39	GEC1/IO116RSB3
40	GEB1/IO114RSB3
41	GEC0/IO115RSB3
42	GEB0/IO113RSB3
43	GEA1/IO112RSB3
44	GEA0/IO111RSB3
45	GEA2/IO110RSB2
46	NC
47	FF/GEB2/IO109RSB2
48	GEC2/IO108RSB2
49	IO106RSB2
50	IO107RSB2
51	IO104RSB2
52	IO105RSB2
53	IO102RSB2
54	IO103RSB2
55	GND
56	VCCIB2
57	IO101RSB2
58	IO100RSB2
59	IO99RSB2
60	IO98RSB2
61	IO97RSB2
62	IO96RSB2
63	IO95RSB2
64	IO94RSB2
65	IO93RSB2
66	VCC
67	IO92RSB2
68	IO91RSB2
69	IO90RSB2

VQ176	
Pin Number	AGLP060 Function
70	IO89RSB2
71	IO88RSB2
72	IO87RSB2
73	IO86RSB2
74	IO85RSB2
75	IO84RSB2
76	GND
77	VCCIB2
78	IO83RSB2
79	IO82RSB2
80	GDC2/IO80RSB2
81	IO81RSB2
82	GDA2/IO78RSB2
83	GDB2/IO79RSB2
84	NC
85	NC
86	TCK
87	TDI
88	TMS
89	VPUMP
90	TDO
91	TRST
92	VJTAG
93	GDA1/IO76RSB1
94	GDC0/IO73RSB1
95	GDB1/IO74RSB1
96	GDC1/IO72RSB1
97	VCCIB1
98	GND
99	IO70RSB1
100	IO69RSB1
101	IO67RSB1
102	IO66RSB1
103	IO65RSB1
104	IO63RSB1

CS201	
Pin Number	AGLP060 Function
H14	IO64RSB1
H15	IO62RSB1
J1	GFA2/IO134RSB3
J2	GFA0/IO135RSB3
J3	GFB2/IO133RSB3
J4	IO131RSB3
J6	VCCIB3
J7	GND
J8	VCC
J9	GND
J10	VCCIB1
J12	IO61RSB1
J13	IO63RSB1
J14	IO68RSB1
J15	IO66RSB1
K1	IO130RSB3
K2	GFC2/IO132RSB3
K3	IO127RSB3
K4	IO129RSB3
K6	GND
K7	VCCIB2
K8	VCCIB2
K9	VCCIB2
K10	VCCIB1
K12	IO65RSB1
K13	IO67RSB1
K14	IO69RSB1
K15	IO70RSB1
L1	IO126RSB3
L2	IO128RSB3
L3	IO121RSB3
L4	IO123RSB3
L12	GDB1/IO74RSB1
L13	GDC1/IO72RSB1
L14	IO71RSB1

CS201	
Pin Number	AGLP060 Function
L15	GDC0/IO73RSB1
M1	IO122RSB3
M2	IO124RSB3
M3	IO119RSB3
M4	GND
M5	IO125RSB3
M6	IO98RSB2
M7	IO96RSB2
M8	IO91RSB2
M9	IO89RSB2
M10	IO82RSB2
M11	GDA2/IO78RSB2
M12	GND
M13	GDA1/IO76RSB1
M14	GDA0/IO77RSB1
M15	GDB0/IO75RSB1
N1	IO117RSB3
N2	IO120RSB3
N3	GND
N4	GEB1/IO114RSB3
N5	IO107RSB2
N6	IO100RSB2
N7	IO94RSB2
N8	IO87RSB2
N9	IO85RSB2
N10	GDC2/IO80RSB2
N11	IO90RSB2
N12	IO84RSB2
N13	GND
N14	TDO
N15	VJTAG
P1	GEC0/IO115RSB3
P2	GEC1/IO116RSB3
P3	GEA0/IO111RSB3
P4	GEA1/IO112RSB3

CS201	
Pin Number	AGLP060 Function
P5	IO106RSB2
P6	IO105RSB2
P7	IO103RSB2
P8	IO99RSB2
P9	IO93RSB2
P10	IO92RSB2
P11	IO95RSB2
P12	IO86RSB2
P13	IO83RSB2
P14	VPUMP
P15	TRST
R1	IO118RSB3
R2	GEB0/IO113RSB3
R3	GEA2/IO110RSB2
R4	FF/GEB2/IO109RSB2
R5	GEC2/IO108RSB2
R6	IO102RSB2
R7	IO101RSB2
R8	IO104RSB2
R9	IO97RSB2
R10	IO88RSB2
R11	IO81RSB2
R12	GDB2/IO79RSB2
R13	TMS
R14	TDI
R15	TCK

CS289	
Pin Number	AGLP030 Function
G10	GND
G11	GND
G12	IO40RSB1
G13	NC
G14	IO39RSB1
G15	IO44RSB1
G16	NC
G17	GND
H1	NC
H2	GEC0/IO108RSB3
H3	NC
H4	IO112RSB3
H5	NC
H6	IO109RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	NC
H13	NC
H14	IO45RSB1
H15	VCCIB1
H16	GDB0/IO48RSB1
H17	IO42RSB1
J1	NC
J2	GEA0/IO107RSB3
J3	VCCIB3
J4	IO105RSB3
J5	NC
J6	NC
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	IO50RSB1

CS289	
Pin Number	AGLP030 Function
J13	IO43RSB1
J14	IO51RSB1
J15	IO52RSB1
J16	GDC0/IO46RSB1
J17	GDA0/IO47RSB1
K1	GND
K2	GEB0/IO106RSB3
K3	IO102RSB3
K4	IO104RSB3
K5	IO99RSB3
K6	NC
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	NC
K13	NC
K14	NC
K15	IO53RSB1
K16	GND
K17	IO49RSB1
L1	IO103RSB3
L2	IO101RSB3
L3	NC
L4	GND
L5	NC
L6	NC
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	IO58RSB1
L13	IO54RSB1
L14	VCCIB1
L15	NC

CS289	
Pin Number	AGLP030 Function
L16	NC
L17	NC
M1	NC
M2	VCCIB3
M3	IO100RSB3
M4	IO98RSB3
M5	IO93RSB3
M6	IO97RSB3
M7	NC
M8	NC
M9	IO71RSB2
M10	NC
M11	IO63RSB2
M12	NC
M13	IO57RSB1
M14	NC
M15	NC
M16	NC
M17	VCCIB1
N1	NC
N2	NC
N3	IO95RSB3
N4	IO96RSB3
N5	GND
N6	NC
N7	IO85RSB2
N8	IO79RSB2
N9	IO77RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	IO59RSB2
N14	NC
N15	GND
N16	IO56RSB1
N17	IO55RSB1
P1	IO94RSB3

Revision	Changes	Page
Revision 12 (continued)	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *IGLOO PLUS FPGA Fabric User's Guide* (SAR 34733).	2-12
	t_{DOUT} was corrected to t_{DIN} in Figure 2-4 • Input Buffer Timing Model and Delays (example) (SAR 37107).	2-16
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34887).	2-27
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36963).	2-58
	Table 2-90 • IGLOO PLUS CCC/PLL Specification and Table 2-91 • IGLOO PLUS CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34820). The value for serial clock was missing from these tables and has been restored. The value and units for input cycle-to-cycle jitter were incorrect and have been restored. The note to Table 2-90 • IGLOO PLUS CCC/PLL Specification giving specifications for which measurements done was corrected from VCC/VCCPLL = 1.14 V to VCC/VCCPLL = 1.425 V. The Delay Range in Block: Programmable Delay 2 value in Table 2-91 • IGLOO PLUS CCC/PLL Specification was corrected from 0.025 to 0.863 (SAR 37058).	2-61, 2-62
	Figure 2-28 • Write Access after Read onto Same Address was deleted. Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 34868). The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-32 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35748).	2-65, 2-68, 2-74, 2-76
	The "Pin Descriptions and Packaging" chapter has been added (SAR 34769).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34769).	4-1
Revision 11 (July 2010)	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOO PLUS Device Status" table indicates the status for each device in the family.	N/A
	The "Reprogrammable Flash Technology" section was revised to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance."	I
	The "I/Os with Advanced I/O Standards" section was revised to add definitions for hot-swap and cold-sparing.	1-6
	Conditional statements regarding hot insertion were removed from the description of VI in Table 2-1 • Absolute Maximum Ratings, since all IGLOO PLUS devices are hot insertion enabled.	2-1

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